



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 60V
- I_D 3A
- D/F2 1/F2 1Tm0 gTmr9((nn)4ON)000008882 0 596.04 842.04 reW* n



YJL03N06AL

■ Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60	-	-	

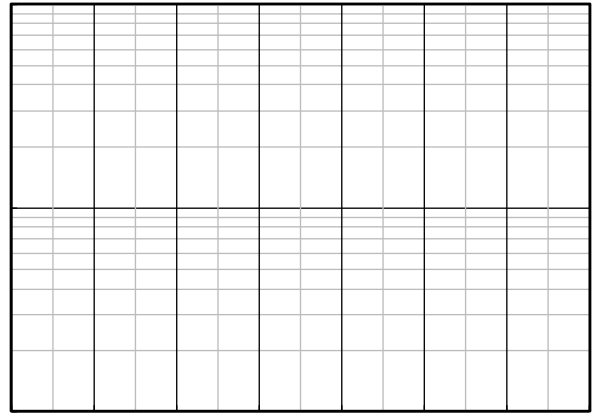
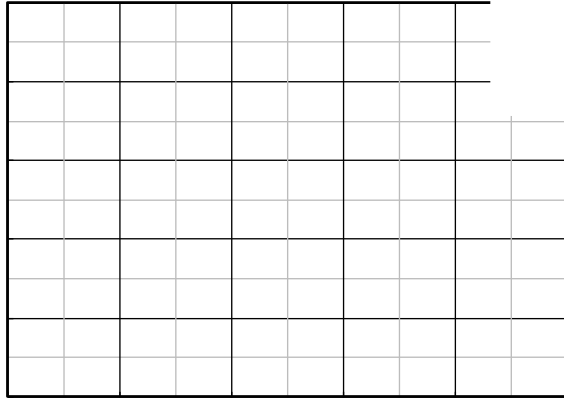
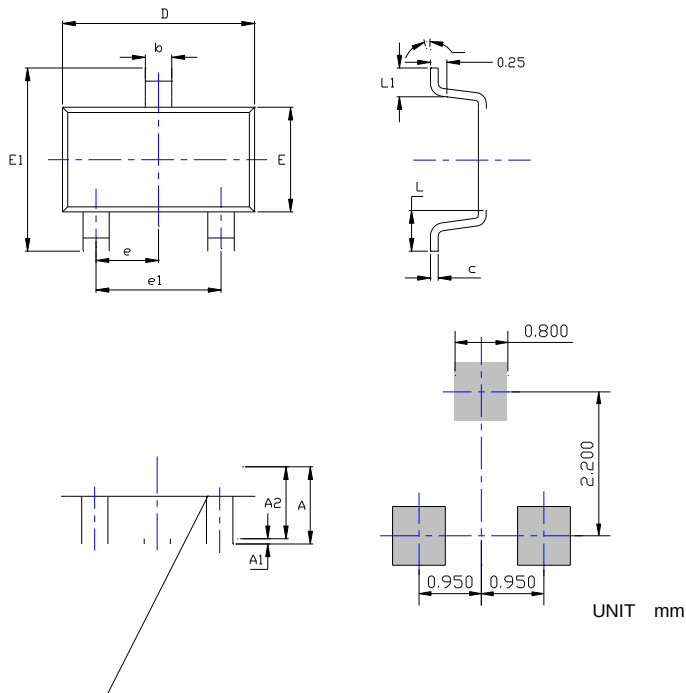


Figure 7. $R_{DS(on)}$ VS Drain Current $I_{DS(on)}$



■ SOT-23-3L Package information





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